

FEATURES

- 8.50 – 9.60 GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +41.5 dBm Output Power at 1dB Compression
- 9.0 dB Power Gain at 1dB Compression
- 35% Power Added Efficiency
- -38 dBc IM3 at $P_o = 30.5$ dBm SCL
- Hermetic Metal Flange Package
- 100% Tested for DC, RF, and R_{TH}



DESCRIPTION

The EID8596-12 is a high power, highly linear, single stage MFET amplifier in a flange mount package. This amplifier features Excelics' unique PHEMT transistor technology.



Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression $f = 8.50\text{-}9.60\text{GHz}$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 3600\text{mA}$	40.5	41.5		dBm
G_{1dB}	Gain at 1dB Compression $f = 8.50\text{-}9.60\text{GHz}$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 3600\text{mA}$	8.0	9.0		dB
ΔG	Gain Flatness $f = 8.50\text{-}9.60\text{GHz}$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 3600\text{mA}$			± 0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 3600\text{mA}$ $f = 8.50\text{-}9.60\text{GHz}$		35		%
I_{d1dB}	Drain Current at 1dB Compression $f = 8.50\text{-}9.60\text{GHz}$		4000	4600	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f = 10\text{ MHz}$ 2-Tone Test; $P_{out} = 30.5\text{ dBm S.C.L.}^2$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 65\% IDSS$ $f = 9.60\text{ GHz}$	-33	-38*		dBc
I_{DSS}	Saturated Drain Current $V_{DS} = 3\text{ V}$, $V_{GS} = 0\text{ V}$		6500	7500	mA
V_P	Pinch-off Voltage $V_{DS} = 3\text{ V}$, $I_{DS} = 60\text{ mA}$		-1.2	-2.5	V
R_{TH}	Thermal Resistance ³		2.5	3.0	$^\circ\text{C/W}$

Notes:

1. Tested with 100 Ohm gate resistor.

2. S.C.L. = Single Carrier Level.

3. Overall R_{th} depends on case mounting.

* These devices are available screened for IM3 performance. Please contact factory with your requirement.



EID8596-12

UPDATED 11/11/2004

8.50 – 9.60 GHz 12-Watt Internally-Matched Power FET

ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION^{1,2}

SYMBOL	CHARACTERISTIC	VALUE
V_{DS}	Drain to Source Voltage	10 V
V_{GS}	Gate to Source Voltage	-3.0 V
I_{DS}	Drain Current	IDSS
I_{GSF}	Forward Gate Current	120 mA
P_{IN}	Input Power	@ 3dB compression
P_T	Total Power Dissipation	42 W
T_{CH}	Channel Temperature	150°C
T_{STG}	Storage Temperature	-65/+150°C

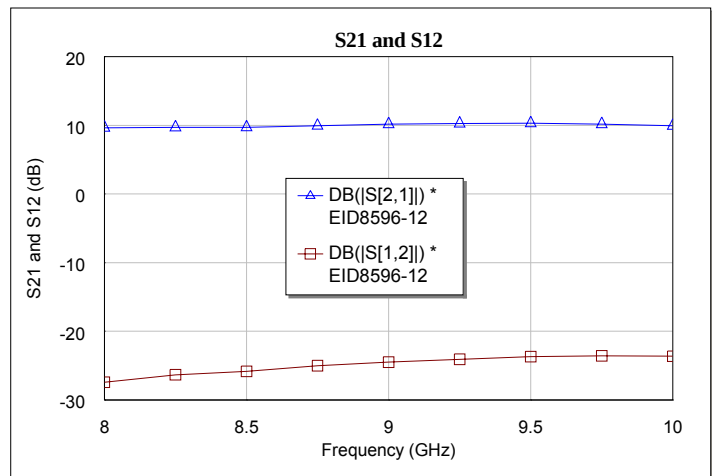
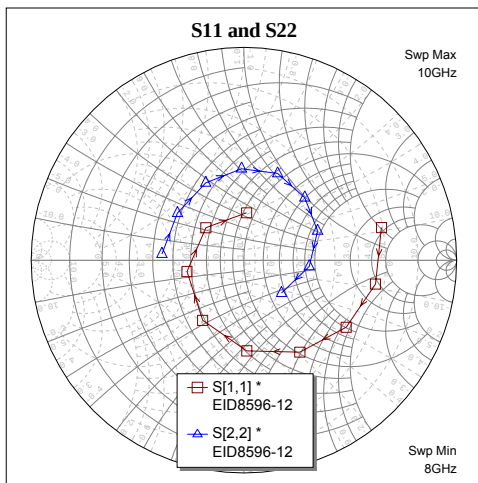
Notes:

- Operating the device beyond any of the above ratings may result in permanent damage or reduction of MTTF.
- Bias conditions must also satisfy the following equation $P_T < (T_{CH} - T_{PKG})/R_{TH}$; where T_{PKG} = temperature of package, and $P_T = (V_{DS} * I_{DS}) - (P_{OUT} - P_{IN})$.

PERFORMANCE DATA

Typical S-Parameters (T= 25°C, 50Ω system, de-embedded to edge of package)

$V_{DS} = 10$ V, $I_{DSQ} \approx 3600$ mA



FREQ (GHz)	--- S11 ---		--- S21 ---		--- S12 ---		--- S22 ---	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
8.00	0.665	13.310	3.042	-101.000	0.043	-143.450	0.386	175.740
8.25	0.628	-10.290	3.060	-126.890	0.048	-171.390	0.383	144.740
8.50	0.575	-33.260	3.064	-151.970	0.051	165.500	0.405	116.280
8.75	0.506	-58.660	3.146	-177.830	0.056	139.920	0.430	91.480
9.00	0.426	-88.220	3.230	154.710	0.060	114.480	0.437	68.710
9.25	0.343	-124.370	3.263	126.660	0.063	87.140	0.410	45.740
9.50	0.273	-168.710	3.280	97.610	0.065	59.430	0.373	21.620
9.75	0.235	139.600	3.232	67.230	0.066	28.560	0.309	-5.450
10.00	0.223	86.780	3.140	36.090	0.066	-1.380	0.235	-41.240
10.25	0.200	27.440	3.023	3.490	0.066	-36.490	0.210	-95.270
10.50	0.209	-47.720	2.818	-30.940	0.063	-72.920	0.291	-146.970

Specifications are subject to change without notice.

Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085

Phone: 408-737-1711 Fax: 408-737-1868 Web: www.excelics.com

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Revised November 2004

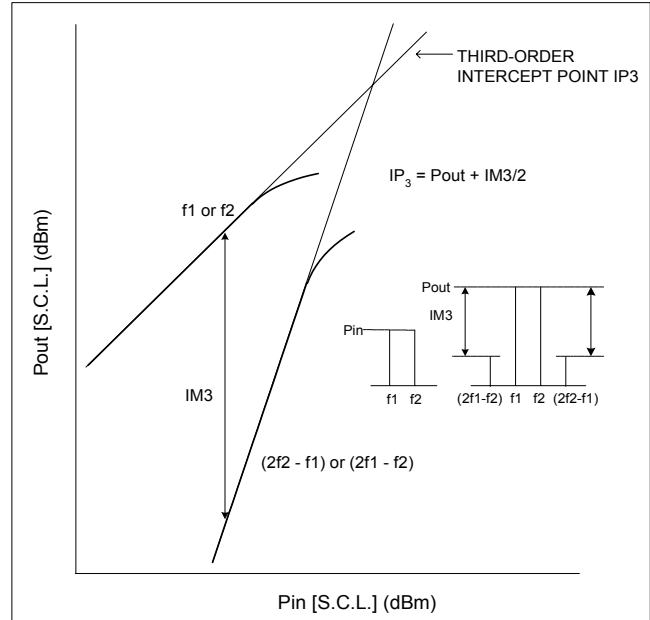
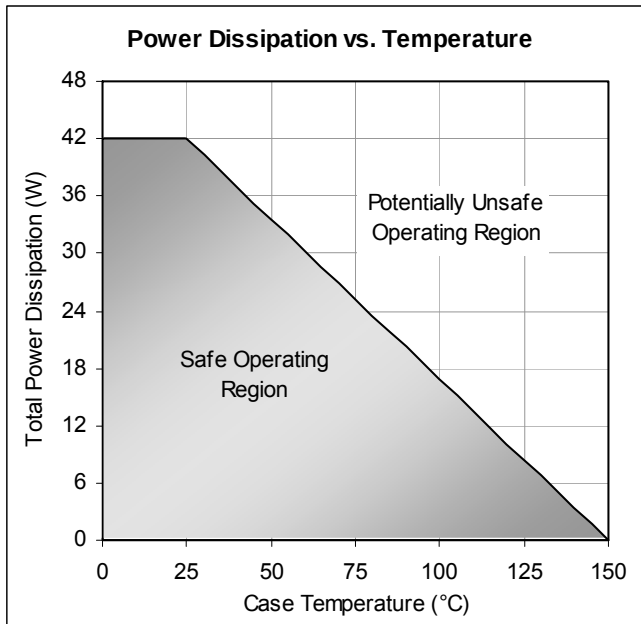


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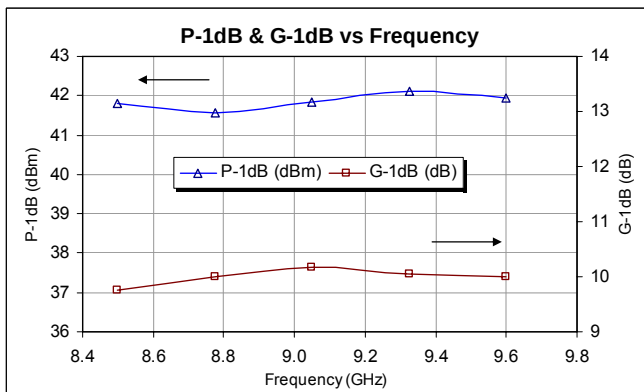
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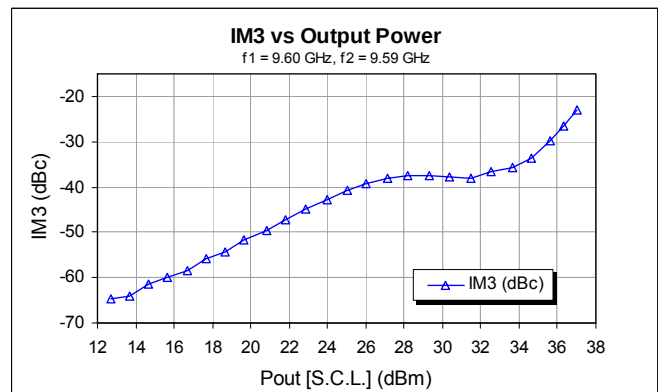
Power De-rating Curve and IM3 Definition



Typical Power Data ($V_{DS} = 10\text{ V}$, $I_{DSQ} = 3600\text{ mA}$)



Typical IM3 Data ($V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 65\% IDSS$)



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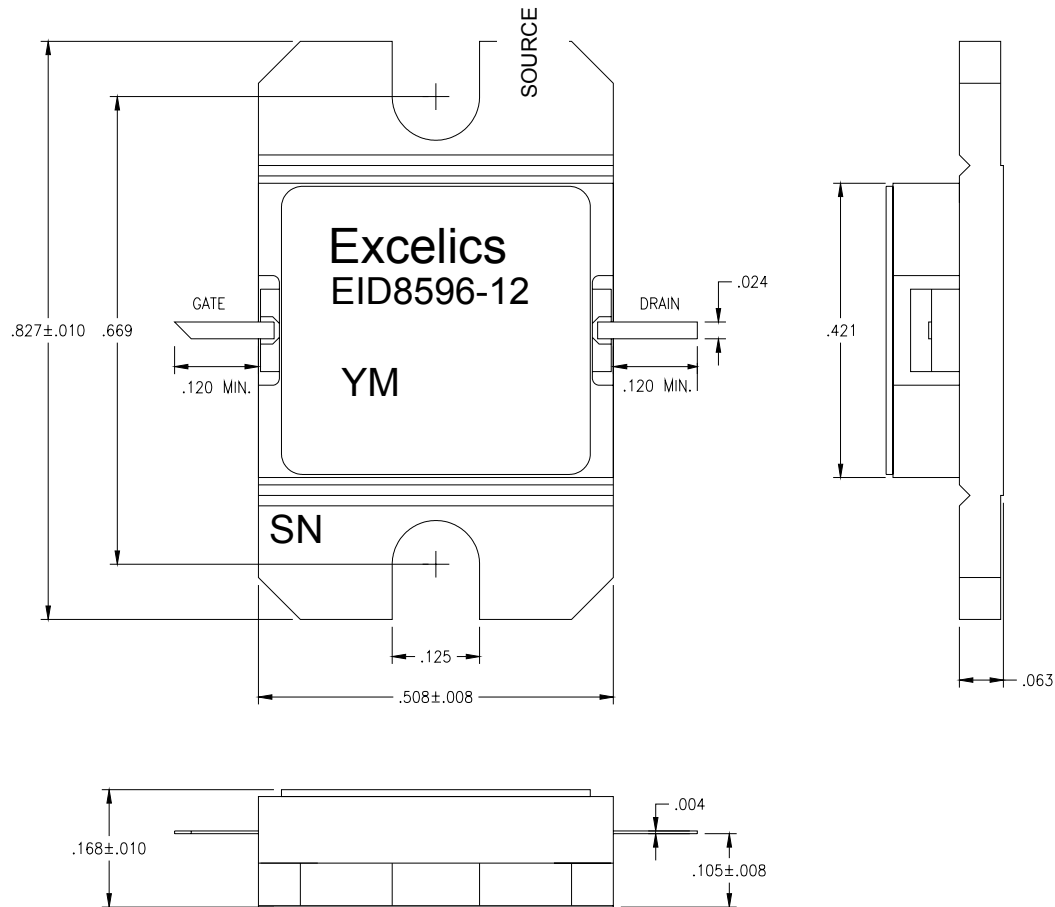
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PACKAGE OUTLINE

Dimensions in inches, Tolerance $\pm .005$ unless otherwise specified



ORDERING INFORMATION

Part Number	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EID8596-12	Industrial	8.50-9.60 GHz	40.5	-33

Notes: 1. Contact factory for military and hi-rel grades.
2. Exact test conditions are specified in "Electrical Characteristics" table.

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